

WHAT IS CLAIMED IS:

1. A method of forming a tunnel oxide film in a semiconductor device,
comprising the steps of:

(a) forming a first oxide film on a semiconductor substrate, and then
5 forming a photo resist pattern exposing the first oxide film in a memory cell
area and a low voltage transistor area;

(b) removing a predetermined thickness of the exposed first oxide film
and the photo resist pattern sequentially; and

(c) removing the remaining first oxide film completely and then
10 forming a second oxide film on a whole surface.

2. The method of claim 1, wherein the first oxide film is a pure oxide
film, and it is grown at a temperature in the range of 750°C to 850°C to have a
thickness in the range of 350 Å to 600 Å.

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3. The method of claim 1, wherein the step (b) further comprises the
steps of:

removing a predetermined thickness of the first oxide film by using a
300:1 BOE for a period in the range of 1,730seconds to 1,735seconds;

20 removing the photo resist pattern by using a H₂SO₄ solution; and
performing a cleaning process using an SC-1 solution to remove
pollutants such as organic components or particles.

4. The method of claim 1, wherein a thickness of the first oxide film remaining after the step (b) is in the range of 17 Å to 23 Å.

5. The method of claim 1, wherein the first oxide film is removed by
5 performing a cleaning process using a 50:1 HF solution in the step (c).